

## REMARKS

Claims 1-3, 5-17, and 36 are pending.

The Examiner rejected Claims 7, 8, 12-16 under 35 U.S.C. 112, first paragraph.

Claims 7 and 12-16 are amended to delete or correct the phrases objected to by the Examiner.

Applicants respectfully submit that all claims meet the requirements of 35 U.S.C. 112.

Applicants thank the Examiner for allowing Claims 1-3, 5, 6, 9-11, 17, and 36.

In view of the above arguments, Applicants respectfully request allowance of all pending claims. Should the Examiner have any questions, the Examiner is invited to call the undersigned at (408) 382-0480.

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Respectfully submitted,

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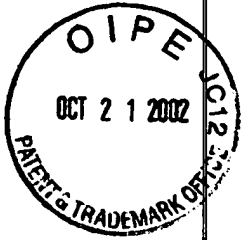
ATTACHMENT A

IN THE CLAIMS

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The claims are amended as follows.

1. (Twice Amended) A light emitting device comprising:  
a substrate;  
an n-type semiconductor layer;  
an active layer for generating light, said active layer being in electrical contact with said n-type semiconducting layer;  
a p-type semiconductor layer in electrical contact with said active layer; and  
a p-electrode in electrical contact with said p-type semiconductor layer, said p-electrode comprising:  
at least a layer of silver having a thickness sufficient to reflect greater than 50% of light incident thereon, wherein a portion of said generated light exits said device through said substrate after being reflected from said p-electrode[, and wherein said p-electrode further comprises];  
a bonding layer in electrical contact with said layer of silver for making electrical connections to said layer of silver; and  
a fixation layer overlying and in electrical contact with said layer of silver.
7. (Amended) The light emitting device of Claim 1 wherein said [p-electrode further comprises a dielectric] fixation layer [overlying said layer of silver] comprises a dielectric.
12. (Amended) The light emitting device of Claim 1 wherein said [p-electrode further comprises a diffusion barrier] fixation layer is disposed between said bonding layer and said layer of silver, said [diffusion barrier] fixation layer providing an electrical path between said bonding layer and said layer of silver, said fixation layer serving as a diffusion barrier layer for preventing constituents from said bonding layer from interdiffusing with said layer of silver.
13. (Amended) The light emitting device of Claim 12 wherein said [diffusion barrier] fixation layer comprises a metal.



14. (Amended) The light emitting device of Claim 13 wherein said [diffusion barrier] fixation layer comprises nickel.

15. (Amended) The light emitting device of Claim 12 wherein said [diffusion barrier] fixation layer encapsulates said layer of silver.

16. (Amended) The light emitting device of Claim 12 wherein said [diffusion barrier] fixation layer is a multi-layered structure.

36. (Twice Amended) A light emitting device comprising:  
a substrate;  
an n-type semiconductor layer;  
an active layer for generating light, said active layer being in electrical contact with said n-type semiconducting layer;  
a p-type semiconductor layer in electrical contact with said active layer; and  
a p-electrode in electrical contact with said p-type semiconductor layer, said p-electrode comprising:  
at least a substantially transparent layer of silver[, and wherein said p-electrode further comprises];  
a bonding layer in electrical contact with said layer of silver for making electrical connections to said layer of silver; and  
a fixation layer overlying and in electrical contact with said layer of silver.

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